

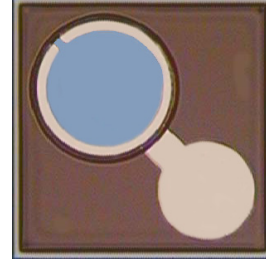
Features

- : AR coated for 850nm
- : Low dark current and low capacitance
- : Data rate 1.25 / 2.5Gbps
- : High reliability
- : Other configurations available on request

Applications

- : High speed Data Communications
- : Gigabit Ethernet
- : Fiber Channel

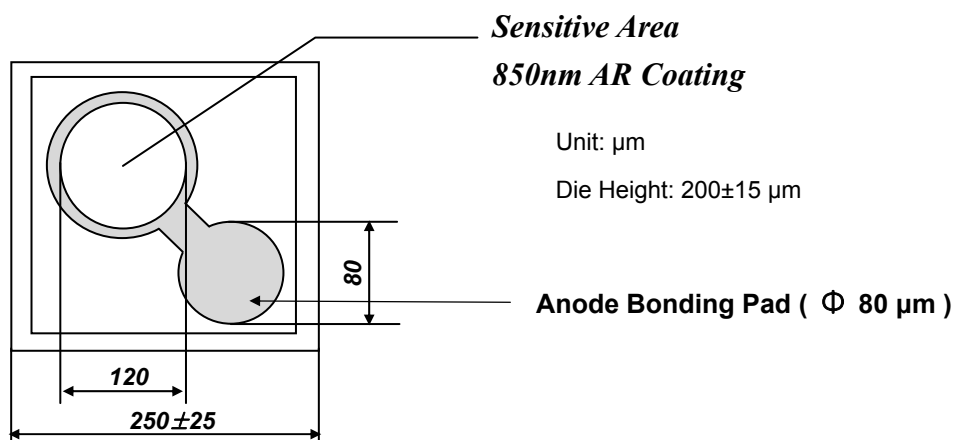
Description



Absolute Maximum Ratings

Parameter	Rating
Forward Current	10mA
Reverse Voltage	40V
Operating Temperature	-20 to 85 °C
Storage Temperature	-40 to 100 °C

Dimensions



Electro-Optics Characteristics (T_a=25°C unless otherwise stated)

Parameters	Symbol	Specified			Unit	Test Conditions
		Min.	Typ.	Max.		
Sensitive Area	D		120		μm	In diameter
Responsivity	R	0.5	0.6		A/W	V _R = 5.0V, λ =850nm
Dark Current	I _D		0.1	1.0	nA	V _R = 5.0V
Breakdown Voltage	V _B	40			V	I _R = 1 μA
Capacitance	C		0.8	1	pF	V _R = 5.0V, f=1MHz
Peak Wavelength	λ		850		nm	
Rise and Fall times	t _r /t _f		100/100		ps	V _R =5V, 20% ~80%
Bandwidth	f _{-3dB}		3.5		GHz	V _R =5V

Notes

- Specific active area, pad size and shapes can be provided on customer's request.

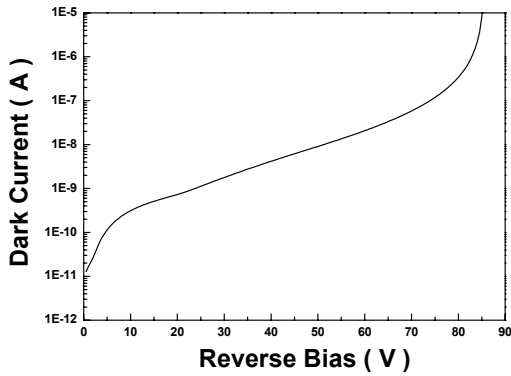
* These specifications are subject to change without notice

NOTICE

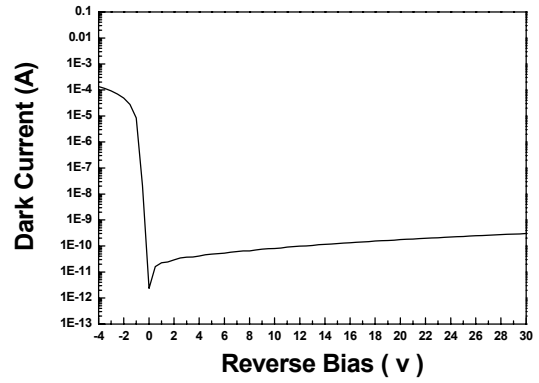
The inherent design of this component causes it to be sensitive to electrostatic discharge(ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product

Characteristics Curves

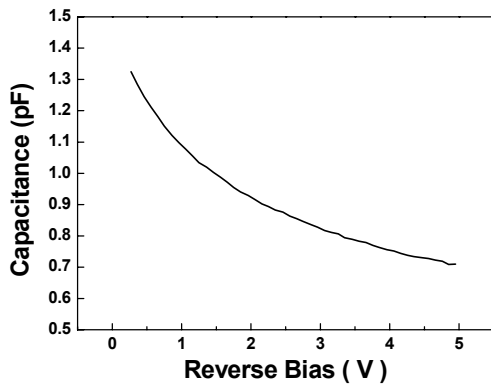
I-V Curve



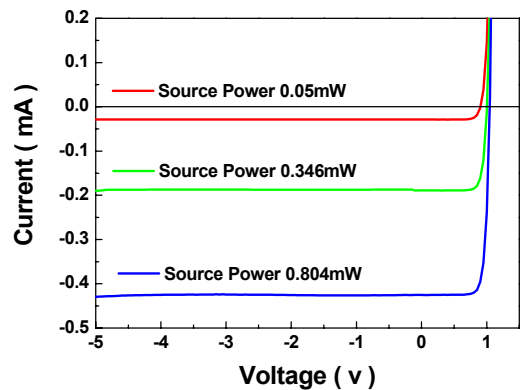
Dark Current



C-V Curve



Responsivity



λ vs Responsivity

